



Product Summary

BVDSS	Rds(on)	ID TA = +25°C
	750mΩ @ V _{GS} = -4.5V	-0.6A
-20V	1050mΩ @ V _{GS} = -2.5V	-0.5A
	1500mΩ @ V _{GS} = -1.8V	-0.45A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP.

- DC-DC converters
- Load switches
- Power-management functions

P-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP2900UWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/guality/product-definitions/

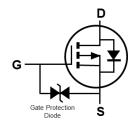
Mechanical Data

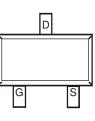
- Package: SOT323
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish—Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.006 grams (Approximate)



SOT323

Top View





Equivalent Circuit

Top View

Ordering Information (Note 4)

Part Number	Backaga	Packing		
Part Nulliber	Package	Qty.	Carrier	
DMP2900UWQ-7	SOT323	3,000	Tape & Reel	
DMP2900UWQ-13	SOT323	10,000	Tape & Reel	

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

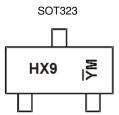
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



HX9 = Product Type Marking Code $\overline{YM} = Date Code Marking$ \overline{Y} = Year (ex: K = 2023) M = Month (ex: 9 = September)

Date Code Key

Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	J	K	L	М	Ν	0	Р	R	S	Т	U	V
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	-	0	0	4	E	C	7	0	0	0	N	Р

Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	Vgss	±6	V
Continuous Drain Current (Note 5) $V_{GS} = 4.5V$	ID	-0.6 -0.5	А
Maximum Body Diode Forward Current (Note 5)	ls	-0.45	A
Pulsed Drain Current (10µs Pulse, Duty Cycle=1%)	I _{DM}	-2.5	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)		PD	0.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	393	°C/W
Total Power Dissipation (Note 5)		PD	0.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	272	°C/W
Operating and Storage Temperature Range	-	TJ, TSTG	-55 to +150	°C

Notes:

Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.

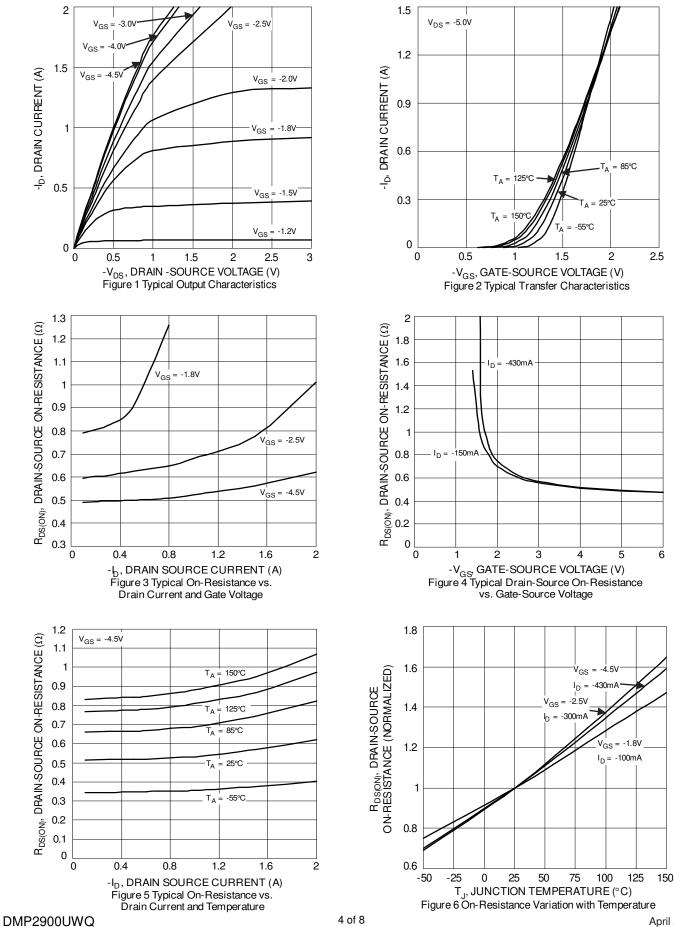


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

			_			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BVDSS	-20	—	—	V	$V_{GS}=0V,\ I_{D}=-250\mu A$
Zero Gate Voltage Drain Current TJ = +25°C	IDSS			-100	nA	$V_{DS} = -20V$, $V_{GS} = 0V$
Gate-Source Leakage	lgss		—	±2.0	μA	$V_{GS} = \pm 4.5 V$, $V_{DS} = 0 V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.5	_	-1.0	V	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$
		_		0.75		$V_{GS} = -4.5V, I_D = -430mA$
Static Drain-Source On-Resistance	R _{DS(ON)}	_		1.05	Ω	$V_{GS} = -2.5V, I_D = -300mA$
		_	—	1.5		VGS = -1.8V, ID = -150mA
Diode Forward Voltage	Vsd	-	_	-1.2	V	V _{GS} = 0V, I _S = -150mA
DYNAMIC CHARACTERISTICS (Note 8)	<u>.</u>					
Input Capacitance	Ciss	_	49	_	pF	
Output Capacitance	Coss	_	12	_	pF	└ V _{DS} = -16V, V _{GS} = 0V - f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	3.4	_	pF	
Total Gate Charge	Qg	_	0.7	_	рС	
Gate-Source Charge	Qgs	_	0.1	_	рС	VGS = -4.5V, VDS = -10V - ID = -250mA
Gate-Drain Charge	Q _{gd}	_	0.1	_	рС	ID = -230IIIA
Turn-On Delay Time	t _{D(on)}	_	16	_	ns	
Turn-On Rise Time	tR	_	15		ns	$V_{DD} = -10V, V_{GS} = -4.5V$
Turn-Off Delay Time	tD(off)		213		ns	$R_L = 47\Omega, R_G = 10\Omega$ $I_D = -200 mA$
Turn-Off Fall Time	t⊨		89		ns	
Reverse Recovery Time	t _{RR}		10.5		ns	
Reverse Recovery Charge	QRR	_	1.8		nC	IF = 1.0A, dl/dt = 100A/µs

 Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing. Notes:



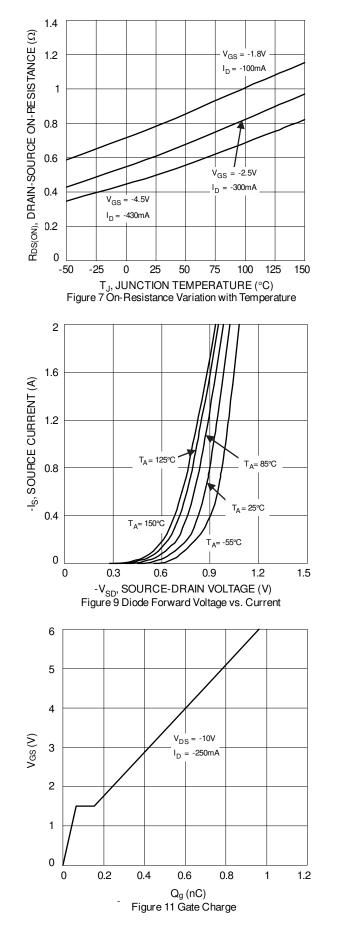


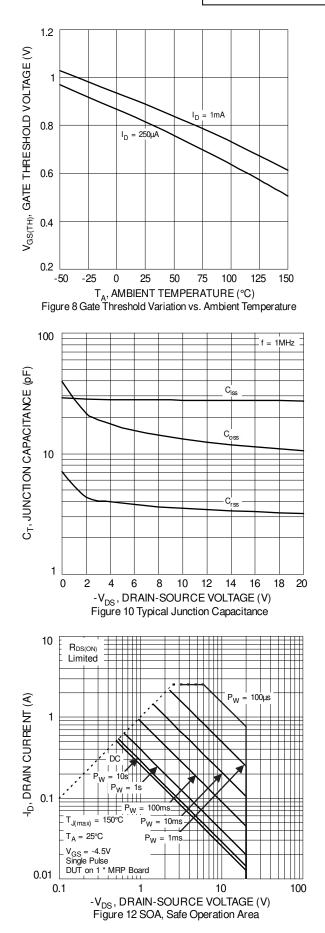
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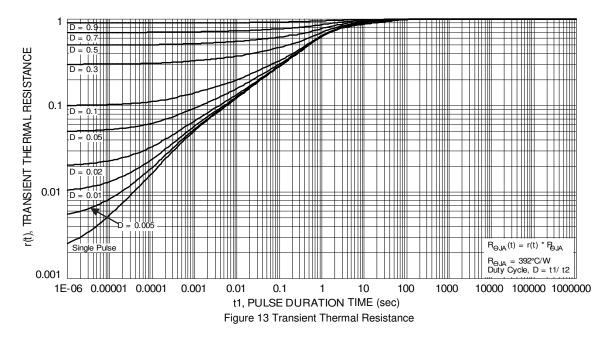






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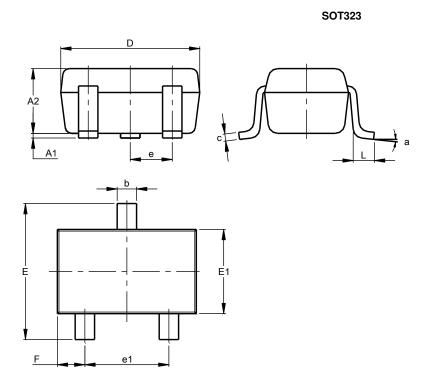






Package Outline Dimensions

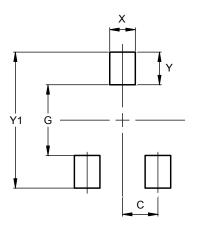
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT323							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.25	0.40	0.30				
С	0.10	0.18	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	C).650 B	SC				
e1	1.20	1.40	1.30				
F	0.375	0.475	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All	Dimen	sions i	in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT323

Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
Y1	2.500



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